

Octal Bus Transceiver

With 5 V-Tolerant Inputs

MC74LVX245

The MC74LVX245 is an advanced high speed CMOS octal bus transceiver.

It is intended for two-way asynchronous communication between data buses. The direction of data transmission is determined by the level of the T/\overline{R} input. The output enable pin (\overline{OE}) can be used to disable the device, so that the buses are effectively isolated.

All inputs are equipped with protection circuits against static discharge.

Features

- High Speed: $t_{PD} = 4.7 \text{ ns}$ (Typ) at $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25 \, ^{\circ}C$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise: V_{OLP} = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 100 mA
- ESD Performance: Human Body Model > 2000 V
- These Devices are Pb-Free and are RoHS Compliant

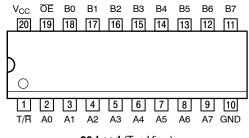
Application Notes

- Do Not Force a Signal on an I/O Pin when it is an Active Output, Damage May Occur
- All Floating (High Impedance) Input or I/O Pins must be Fixed by Means of Pullup or Pulldown Resistors or Bus Terminator ICs
- A Parasitic Diode is Formed between the Bus and V_{CC} Terminals
 Therefore, the LVX245 cannot be Used to Interface 5.0 V to 3.0 V
 Systems Directly



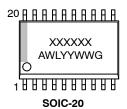


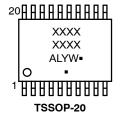
PIN ASSIGNMENT



20-Lead (Top View)

MARKING DIAGRAMS





XXXXXXX = Specific Device Code A = Assembly Location

WL, L = Wafer Lot Y = Year WW, W = Work Week G or • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

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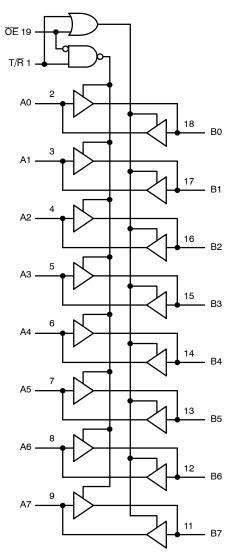


Figure 1. Logic Diagram

Table 1. PIN NAMES

Pins	Function
OE	Output Enable Input
T/R	Transmit/Receive Input
A0-A7	Side A 3-State Inputs or 3-State Outputs
Bo-B7	Side B 3-State Inputs or 3-State Outputs

Inp	uts	Operating Mode
OE	T/R	Non-Inverting
L	L	B Data to A Bus
L	Н	A Data to B Bus
Н	Х	Z

H = High Voltage Level;
L = Low Voltage Level;
Z = High Impedance State;
X = High or Low Voltage Level and Transitions are Acceptable;
For I_{CC} reasons, Do Not Float Inputs

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +6.5	V
V _{IN}	DC Input Voltage		-0.5 to +6.5	V
V _{OUT}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IN}	DC Input Current, per Pin		±20	mA
I _{OUT}	DC Output Current, Per Pin		±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins		±75	mA
I _{IK}	Input Clamp Current		-20	mA
lok	Output Clamp Current		±20	mA
T _{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 secs		260	°C
T_J	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SOIC-20W TSSOP-20	96 150	°C/W
P _D	Power Dissipation in Still Air at 25 °C	SOIC-20W TSSOP-20	1302 833	mW
MSL	Moisture Sensitivity	SOIC-20W All Other Packages	Level 3 Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.573 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 N/A	V
I _{LATCHUP}	Latchup Performance (Note 4)		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Applicable to devices with outputs that may be tri-stated.
- 2. Measured with minimum pad spacing on an FR4 board, using 76 mm-by-114 mm, 2-ounce copper trace no air flow per JESD51-7.
- 3. HBM tested to EIA / JESD22-A114-A. CDM tested to JESD22-C101-A. JEDEC recommends that ESD qualification to EIA/JESD22-A115A (Machine Model) be discontinued.
 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	3.6	V
V _{in}	DC Input Voltage (T/R, OE)	0	5.5	V
V _{I/O}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-40	+85	°C
Δt/ΔV	Input Rise and Fall Time	0	100	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			v _{cc}	T,	_A = 25 °	С	T _A = -40	to 85 °C	
Symbol	Parameter	Test Conditions	VCC	Min	Тур	Max	Min	Max	Unit
V _{IH}	High-Level Input Voltage		2.0 3.0 3.6	1.5 2.0 2.4			1.5 2.0 2.4		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 3.6			0.5 0.8 0.8		0.5 0.8 0.8	V
V _{OH}	High-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$\begin{split} I_{OH} &= -50 \; \mu\text{A} \\ I_{OH} &= -50 \; \mu\text{A} \\ I_{OH} &= -4 \; \text{mA} \end{split}$	2.0 3.0 3.0	1.9 2.9 2.58	2.0 3.0		1.9 2.9 2.48		V
V _{OL}	Low-Level Output Voltage (V _{in} = V _{IH} or V _{IL})	$\begin{split} I_{OL} &= 50 \; \mu\text{A} \\ I_{OL} &= 50 \; \mu\text{A} \\ I_{OL} &= 4 \; \text{mA} \end{split}$	2.0 3.0 3.0		0.0 0.0	0.1 0.1 0.36		0.1 0.1 0.44	V
l _{in}	Input Leakage Current	$V_{in} = 5.5 \text{ V or GND}$ $(T/\overline{R}, \overline{OE})$	3.6			±0.1		±1.0	μΑ
I _{OZ}	Maximum 3-State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	3.6			±0.2 5		±2.5	μΑ
I _{CC}	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

				T,	_A = 25 °	С	T _A = -40	to 85 °C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay Input to Output	V _{CC} = 2.7 V	C _L = 15 pF C _L = 50 pF		6.1 8.6	10.7 14.2	1.0 1.0	13.5 17.0	ns
		$V_{CC} = 3.3 \pm 0.3 \text{ V}$	C _L = 15 pF C _L = 50 pF		4.7 7.2	6.6 10.1	1.0 1.0	8.0 11.5	
t _{PZL} , t _{PZH}	Output Enable Time to High and Low Level	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 15 pF C _L = 50 pF		9.0 11.5	16.9 20.4	1.0 1.0	20.5 24.0	ns
		V_{CC} = 3.3 ± 0.3 V R_L = 1 k Ω	C _L = 15 pF C _L = 50 pF		7.1 9.6	11.0 14.5	1.0 1.0	13.0 16.5	
t _{PLZ} , t _{PHZ}	Output Disable Time From High and Low Level	$V_{CC} = 2.7 \text{ V}$ $R_L = 1 \text{ k}\Omega$	C _L = 50 pF		11.5	18.0	1.0	21.0	ns
		V_{CC} = 3.3 ± 0.3 V R_L = 1 k Ω	C _L = 50 pF		9.6	12.8	1.0	14.5	
toshl toslh	Output-to-Output Skew (Note 5)	V _{CC} = 2.7 V V _{CC} = 3.3 ±[0.3 V				1.5 1.5		1.5 1.5	ns

Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device.
 The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

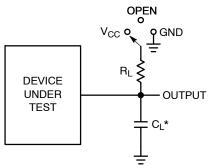
CAPACITIVE CHARACTERISTICS

		T,	_A = 25 °	С	T _A = -40	to 85 °C	
Symbol	Parameter	Min	Тур	Max	Min	Max	Unit
C _{in}	Input Capacitance (T/R, OE)		4	10		10	pF
C _{I/O}	Maximum 3-State I/O Capacitance		8				pF
C _{PD}	Power Dissipation Capacitance (Note 6)		21				pF

^{6.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

$\textbf{NOISE CHARACTERISTICS} \text{ (Input } t_{\text{f}} = t_{\text{f}} = 3.0 \text{ ns, } C_{\text{L}} = 50 \text{ pF, } V_{\text{CC}} = 3.3 \text{ V, Measured in SOIC Package)}$

		T _A = 25 °C		
Symbol	Characteristic	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.5	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.5	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		2.0	V
V_{ILD}	Maximum Low Level Dynamic Input Voltage		0.8	V



÷	
*C _L Includes probe and jig capacitance	

Test	Switch Position	CL	R _L
t _{PLH} / t _{PHL}	Open	See AC Charact	1 kΩ
t _{PLZ} / t _{PZL}	V _{CC}	eristics	
t _{PHZ} / t _{PZH}	GND	Table	

Figure 2. Test Circuit

SWITCHING WAVEFORMS

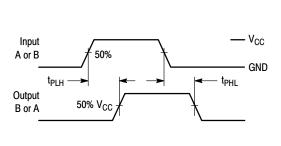


Figure 3.

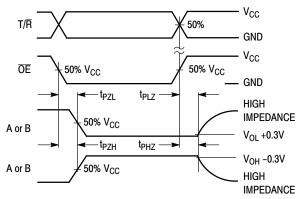


Figure 4.

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
MC74LVX245DWR2G	LVX245G	SOIC-20 WB	1000 / Tape & Reel
MC74LVX245DTR2G	LVX 245	TSSOP-20	2500 / Tape & Reel

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

REVISION HISTORY

Revision	Description of Changes	Date
7	Modified voltage ratings from 7.0 V to 6.5 V.	07/09/2025

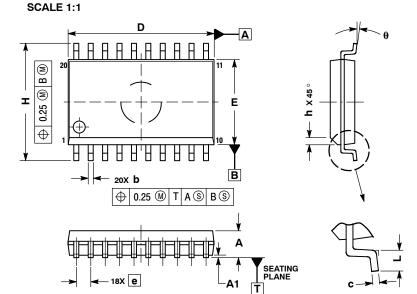
This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.





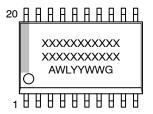
SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
b	0.35	0.49	
С	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
A	0 °	7 °	



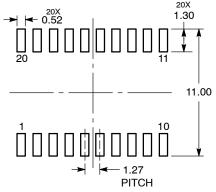
GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

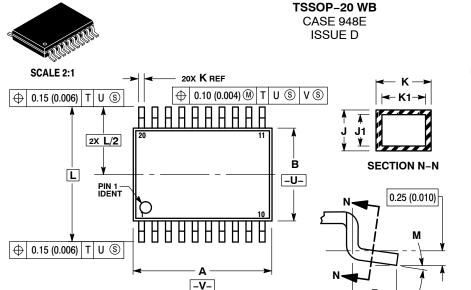
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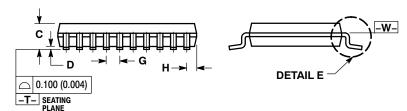
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DATE 17 FEB 2016







DETAIL E

NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

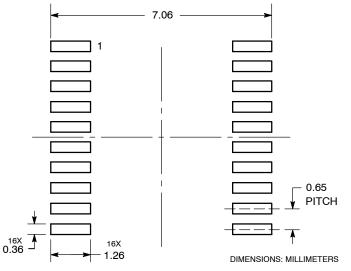
 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

 4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL CONDITION.
 TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

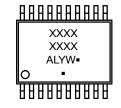
	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
7	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot

= Year

= Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	TSSOP-20 WB		PAGE 1 OF 1

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